# Optical Detection of Quantum Dot Single-Electron Tunneling

#### UNIVERSITÄT DUISBURG ESSEN

Offen im Denken

A. Kurzmann<sup>1,3</sup>, P. Stegmann<sup>1</sup>, J. Kerski<sup>1</sup>, A. Ludwig<sup>2</sup>, A. D. Wieck<sup>2</sup>, J. König<sup>1</sup>, M. Geller<sup>1</sup>, and A. Lorke<sup>1</sup> <sup>1</sup>Faculty of Physics and CENIDE, University of Duisburg-Essen, Lotharstr. 1, 47057 Duisburg, Germany <sup>2</sup>Chair of Applied Solid State Physics, Ruhr-Universität Bochum, Universitätsstr. 150, 44780 Bochum, Germany <sup>3</sup>Solid State Physics Laboratory, ETH Zürich, 8093 Zürich, Switzerland

CENTER FOR NANOINTEGRATION DUISBURG-ESSEN



#### 1. Motivation

Optical measurements
Resonance fluorescence (RF) of a single quantum dot (QD)

Transport measurements
 Characterization of tunneling processes in a single QD
 Full counting statistics (FCS)



#### 2. Sample and set-up



- Resonance fluorescence setup with linear polarizers to separate laser excitation and QD emission
- 10<sup>7</sup> laser background suppression



Is it possible to observe every tunneling event into a single self-assembled QD?
Correlation and interaction in full counting statistics (FCS) with factorial cumulants [3]

Si-doped GaAs as charge reservoir
 45 nm AlGaAs/GaAs tunneling barrier
 QD can be charged with single charge resolution



# 3. Quantum jumps of single electron tunneling

Resonance fluorescence of the fine-structure splitted exciton



Nuclear spin polarization in an magnetic field

Time-resolved RF of the Exciton (X) while an electron tunnels into the QD



# 4. Tunneling rates



Stabilization of the resonant excitation on the exciton transition



- The electron in the QD switches the resonance fluorescence signal off and on
- We observe quantum jumps of the electron tunneling
- into and out of the dot
- Time-resolution: 100 μs



Tunneling rate into the QD exceeds the tunneling rate for electron tunneling out of the dot by a factor of two, due to spin degeneracy [4]

## 5. Counting statistics and spin relaxation



Factorial cumulants [5,6]

B= 4 T

γ<sub>↑↓</sub>=`3 ms<sup>-1</sup>

$$C_{F,m}(t) = \partial z^m ln M_F(z,t) \Big|_{z=0}$$
 with  $M_F(z,t) = \sum_{n=0}^{\infty} (z+1)^n P_N(t)$ 

• ... are more sensitive to interactions between the charge carriers • Factorial cumulants in a three-state model with spin relaxation  $\gamma_{\uparrow\downarrow}$ 

 $--\gamma_{\uparrow\downarrow} = \infty - - \gamma_{\uparrow\downarrow} = 3 \text{ ms}^{-1} - \gamma_{\uparrow\downarrow} = 1 \text{ ms}^{-1} - - \gamma_{\uparrow\downarrow} = 0$ 



#### 6. Conclusion



- Optical measurements of the electron tunneling dynamics
- Single-electron tunneling events (quantum jumps) in a RF telegraph signal
- Full counting statistics demonstrates Sub-Poissonian distribution for equal tunneling rates
- Factorial cumulants enable to observe the spin dynamics in an equilibrium charge measurement

## Further reading

[1] Matthiesen et al., Phys. Rev. Lett. **108**, 093602 (2012).
[2] Gustavsson et al., Phys. Rev. Lett. **96**, 076605 (2006).
[3] Kurzmann et al., Phys. Rev. Lett. **122**, 247403 (2019).
[4] Kurzmann et al, Phys. Rev. Lett. **117**, 017401 (2016).
[5] Stegmann et al., Phys. Rev. B **92**, 155413 (2015).
[6] Stegmann et al., Phys. Rev. B **94**, 125433 (2016).

contact: martin.geller@uni-due.de